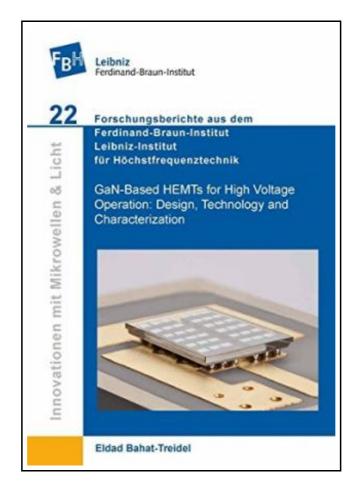
# GaN-Based HEMTs for High Voltage Operation: Design, Technology and Characterization



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### GAN-BASED HEMTS FOR HIGH VOLTAGE OPERATION: DESIGN, TECHNOLOGY AND CHARACTERIZATION



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